

ABSTRACT OF THE DISCLOSURE

A surface of a glass plate is coated with a first n-type semiconductor film which is a 50 nm-thick niobium oxide film as a primer layer. The primer layer is coated with a 250 nm-thick photocatalyst film comprising titanium oxide. Thus, an article having a photocatalytically active surface is obtained. The two coating films can be formed by sputtering. The first n-type semiconductor film as the primer layer is selected so as to have a larger energy band gap than the titanium oxide. Due to this constitution, more holes are generated near the film surface. This article can be free from the problem of conventional titanium oxide films having photocatalytic activity that it is difficult to generate many surface holes contributing to photocatalytic activity, because electrons and holes generated by charge separation recombine within the film, making it impossible to effectively heighten catalytic activity.